ESTM/AFM Observations on Si(111) in Several Solutions

Atsushi ANDO1, Kazuaki MIKH1, Tetsuo SHIMIZU1,*, Kazuhiko MATSUMOTO1,
Yukinori MORITA2 and Hiroshi TOKUMOTO1,2
1Electrotechnical Laboratory (ETL), 1-1-4 Umezono, Tsukuba, Ibaraki 305, Japan
2National Institute for Advanced Interdisciplinary Research (NAIR),
1-1-4 Higashi, Tsukuba, Ibaraki 305, Japan

Electrochemical scanning tunneling microscopy (ESTM) and atomic force microscopy (AFM) measurements were performed to observe topographies on hydrogen-terminated Si(111) surfaces in several solutions. In a dilute H2SO4 solution, AFM images were similar to ESTM ones. This result indicates that the AFM observation is a useful method to study topographies with a possible application to insulating materials. We have also shown AFM images of H-Si(111) in ultrapure water and in a dilute NaOH solution.

1. INTRODUCTION

Silicon is one of major semiconductor materials which is widely used for many kinds of electronic devices. Recently, it was pointed out that atomic-scale surface flatness of the Si substrate is important for fabricating microstructural electronic devices using the Si ULSI technologies5. As one of the methods to solve this problem, wet processes have been of interest. To examine surface flatness of Si(111) treated by a wet process, many studies have been performed by using ultrahigh vacuum scanning tunneling microscopy (UHV-STM)13 and atomic force microscopy (AFM)9. These studies are mainly ex situ observations. For further studies about wet processes of Si substrates, study on topographic change during a wet process is important and in situ observation of Si surfaces in solutions is necessary. A number of studies about in situ observation of Si(111) surfaces have been reported using electrochemical STM (ESTM)6–15. Though ESTM is a very useful method for in situ observation in solutions, it has some disadvantages. The bias voltage is limited to observe surfaces with stability and without surface modification. Moreover, it is impossible to apply ESTM to a specimen covered with thick insulating layers such as SiO2. On the contrary, AFM is a powerful method for observation under such conditions. From this point of view, AFM observation of Si surfaces in solutions is important but only a few studies have been reported10. As the first stage of our studies, we have demonstrated the performance of AFM observation for observing the images of H-terminated p-Si(111) surfaces in a dilute H2SO4 solution, in ultrapure water and in a dilute NaOH solution.

*present address : National Institute for Advanced Interdisciplinary Research (NAIR)

2. EXPERIMENTAL

Highly B-doped (1x1018/cm3)p-Si(111) specimens (Shin-ETSu Semiconductors Co., Ltd.) were used for observation. Those surfaces had vicinalities less than ± 0.1° from the (111) direction. After degreasing with acetone in ultrasonic cleaner, the specimens were boiled in a 2:1 solution of H2SO4:H2O at 100°C for 10 min. After these processes, the specimens were dipped into a 40% NH3F solution for 40 min to terminate the surfaces by hydrogen atoms. After above-mentioned treatments, all specimens were placed into sample cell in a glove bag purged with dry N2 gas and then were covered with ultrapure water (>18.3 MΩ cm, Millipore-Q). These preparations enabled us to examine surfaces without exposing to air. A dilute H2SO4 solution and a dilute NaOH solution were prepared by dropping reagent solutions (supercure grade, KANTO Chem. Co., Ltd.) into the ultrapure water that covered the surface of the specimen. ESTM and AFM observations were performed with commercial units (ESTM; STE330, AFM; SPA300, Seiko Instruments Inc.). All images shown in this study were topographic ones. The ESTM tips were prepared by electrochemical etching of a Pt wire, subsequently by insulating with apiezon wax. Cantilevers (a spring constant of 0.09 N/m) with a microfabricated silicon nitride tip (Olympus Optical Co., Ltd.) were used for AFM observation. The reference force during AFM measurement was maintained at the order of 10-4 N.

3. RESULTS AND DISCUSSION

3.1. ESTM and AFM IMAGES IN A DILUTE H2SO4 SOLUTION

ESTM and AFM images on H-Si(111) surfaces in a
dilute H$_2$SO$_4$ solution are shown in Figs. 1 (a) and (b), respectively. The scanning area of the two images is 450 x 450 nm$^2$. Few absorbed contaminants are observed on these surfaces. The ESTM and AFM images exhibit some common features as the follows: The surfaces consist of successive monolayer-height terraces toward the $<11\bar{2}>$ direction. There are triangular monolayer-depth holes whose sides are toward the $<1\bar{1}2>$ direction. These characteristic features of the AFM image are also in good agreement with the previous STM studies on H-Si(111)$^{23}$. This result indicates that the AFM image seems to reflect the topography of Si surface and we can compare the AFM result with the ESTM one.

Later after the observation of Fig. 2 (a). The area of this image is also 450 x 350 nm$^2$. White arrows in Figs. 2 (a) and (b) indicate the same points. The overall feature of these images is similar but the change of step edge can be clearly observed at an area indicated by the white arrow. It was also observed that the other step edges partially backed about 10 nm. The tendency of step changes is independent on reference forces and interval of AFM measurement. We confirmed that this change was not caused by mechanical modification such as scratching by tip. However the effect of mechanical modification still remains and we can not discuss in detail because the resolution of the AFM image shown in Fig. 2 (b) became worse during continuous measurements, which suggests cantilever tip might be damaged.

3.2. AFM IMAGES IN ULTRAPURE WATER

Figure 2 (a) shows typical, 450 x 350 nm$^2$, AFM image of as-prepared specimens in ultrapure water. The overall feature of this image is similar to that shown in Fig. 1 (b). The ESTM measurement is difficult in ultrapure water because of insufficiency of electrolytes. AFM images in ultrapure water could be obtained easily. This is one of advantage points of AFM measurement compared with ESTM method.

From continuous AFM measurement, we found the change of step edge. Figure 2 (b) was observed 1 hour later after the observation of Fig. 2 (a). The area of this image is also 450 x 350 nm$^2$. White arrows in Figs. 2 (a) and (b) indicate the same points. The overall feature of these images is similar but the change of step edge can be clearly observed at an area indicated by the white arrow. It was also observed that the other step edges partially backed about 10 nm. The tendency of step changes is independent on reference forces and interval of AFM measurement. We confirmed that this change was not caused by mechanical modification such as scratching by tip. However the effect of mechanical modification still remains and we can not discuss in detail because the resolution of the AFM image shown in Fig. 2 (b) became worse during continuous measurements, which suggests cantilever tip might be damaged.

3.3. AFM IMAGES IN A DILUTE NaOH SOLUTION

We also performed AFM observation in a dilute NaOH solution. As soon as NaOH reagent was dropped, the first stage of the etching process occurred. We observed at first that there were triangular holes whose sides consisted of a few monolayer-height terraces toward the $<1\bar{1}2>$ direction. We can not reveal the sites where the etching starts, because the stability of AFM measurement became worse for a few minutes because of NaOH diffusion. As the etching proceeded, these holes became larger. Figure 3 (a) is typical, 500 x 500 nm$^2$, image observed during surface etching proceeding. All triangular holes observed on the terraces are monolayer-depth and the directions of those sides are toward the $<1\bar{1}2>$ direction. As the etching proceeded, the size of the holes became larger with holding the
direction on the new triangular etching also observed that the etching proceeds changed. To hydrogen-silicon bonds between step changes.

For surface a initial investigated typical, anisotropic etching in the number was not observed Si specimen at 1x10^13/cm^2. Figure 3 (a) shows a typical, 500 x 500 nm^2, image of dopants-changed Si surface in a dilute NaOH solution. The significant changes were not observed as compared with Fig. 3 (a). For the formation mechanism, further studies are necessary.

The anisotropic etching process of Si(111) was investigated by Allongue et al., who observed the initial stage of n-Si(111) etching at near open circuit potential (OCP) by ESTM. They reported that in situ ESTM measurement was difficult at the OCP because of the surface reactivity. By using AFM, we could stably and continuously perform in situ observation on unbiased Si(111) specimen. This suggests that AFM measurement is useful to observe under the conditions which ESTM measurement is difficult.

4. CONCLUSION

Hydrogen-terminated Si(111) surfaces in several solutions were studied by using ESTM and AFM and we demonstrated the performance of AFM observation in solutions. The AFM technique is a powerful method to study surface dynamics during chemical reactions with a possible application to insulating materials. In this paper, we showed AFM images of H-Si(111) in a dilute H2SO4 solution, in ultrapure water and in a dilute NaOH solution. The detailed studies on Si surfaces in solutions are now in progress.

REFERENCES